

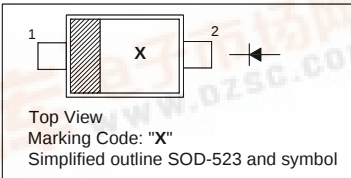
SDB720WT

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for high speed switching circuit and small current rectification applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

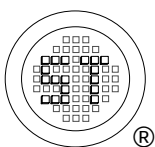
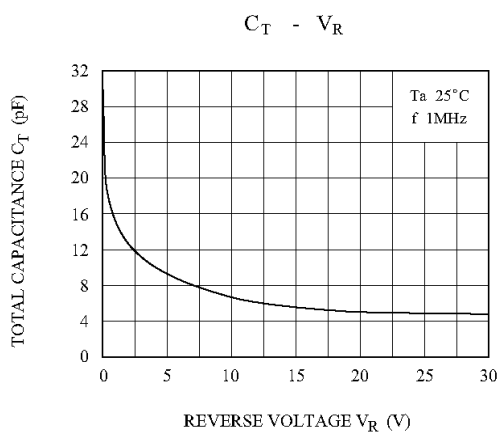
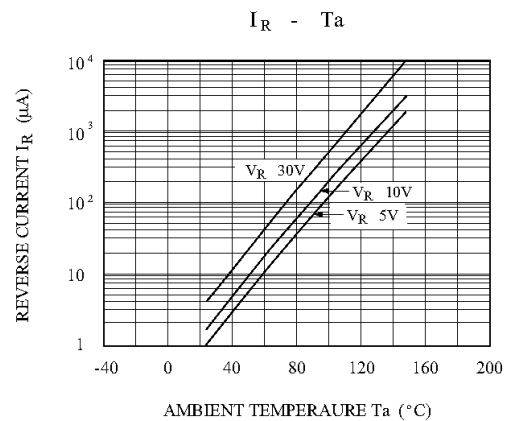
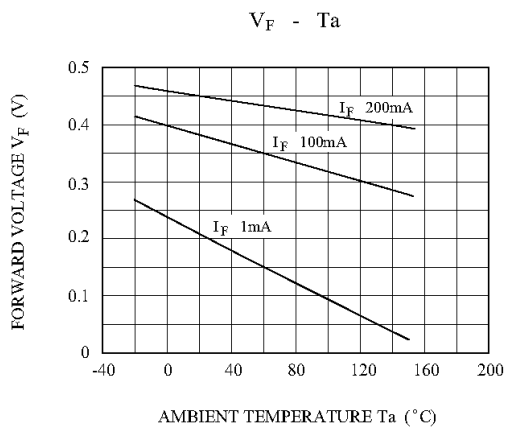
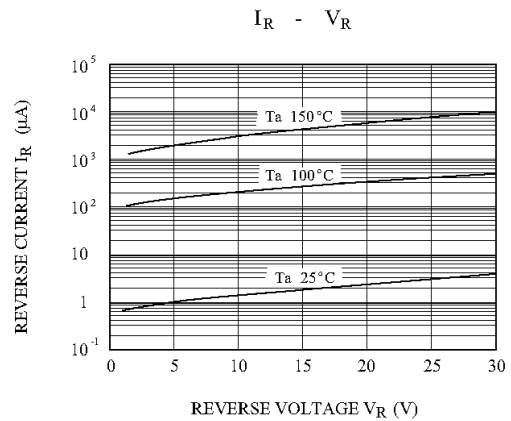
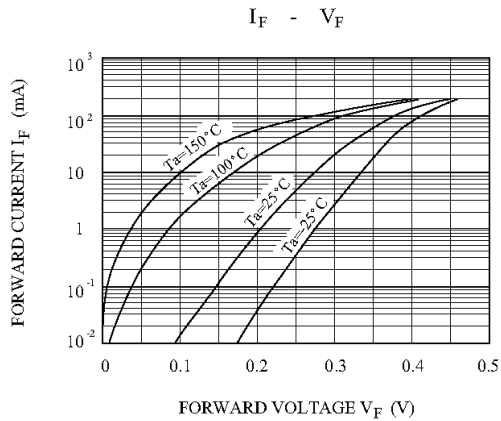
Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	30	V
Average Forward Current	I _O	200	mA
Non-repetitive Peak Forward Surge Current	I _{FSM}	1	A
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 200 mA	V _F	0.5	V
Reverse Current at V _R = 10 V	I _R	30	μA

SDB720WT

查询"SDB720WT"供应商



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

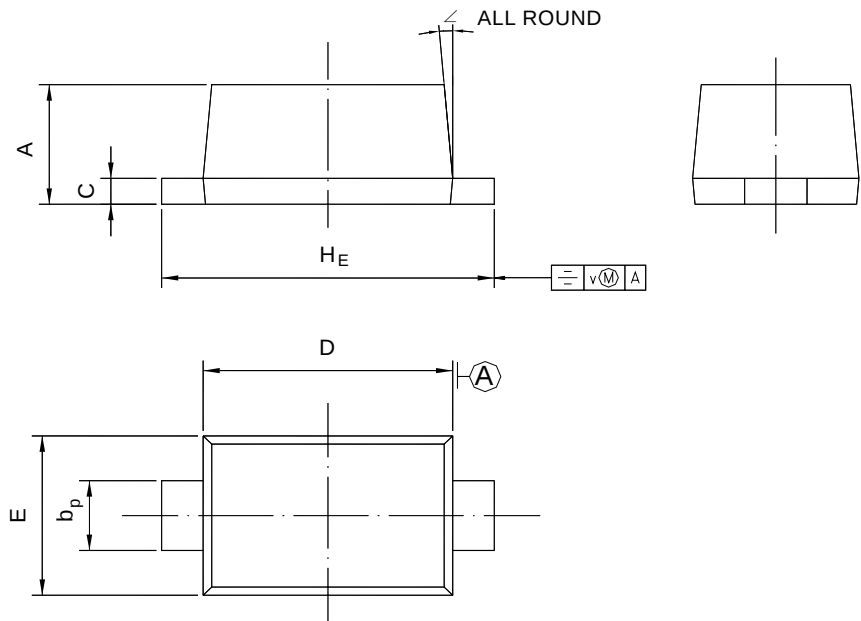


Dated : 06/12/2006

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

